#31/9 VIIIOU PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hisashi OHTANI et al.

Serial No.: 08/807,737

Filed: February 27, 1997

For: METHOD FOR

**MANUFACTURING** 

SEMICONDUCTOR DEVICE

Group Art Unit: 2813

Examiner: M. Sulsky

## CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents and Trademarks, Washington, D.C. 20231, on 3-31-00.

Deborat Toyal

## **AMENDMENT**

Assistant Commissioner for Patents Washington, D. C. 20231

Sir:

In response to the Office Action mailed October 4, 1999, please amend the above-identified application as follows.

## **IN THE CLAIMS:**

Please add the following new claims 78-83:

- --78. A method according to claim 19 wherein said silicon nitride film is in contact with said semiconductor film.
- 79. A method according to claim 24 wherein said silicon nitride film is in contact with said semiconductor film.
- 80. A method according to claim 36 wherein said-silicon nitride film is in contact with said semiconductor film.

4 81. A method according to claim 60 wherein said silicon nitride film is in contact with said semiconductor film.

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